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Initial\* No

Application Number		10596327
Filing Date		2004-11-24
First Named Inventor MARS		SH et al.
Art Unit		2828
Examiner Name	Not Y	et Assigned
Attorney Docket Number		35832,000127

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			U.S.P	ATENT APPLI	CATION PUB	LICATIONS		
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	1	TAEK, Y, et al., 'Effect of dielectric -semiconductor capping layer combination on the dielectric cap quantum well disordering of InGeAsInGaAsP quantum well structure", Technical Digest CLEO / Pacific Rm '99, Pacific Rm Conference on Lesers and Electro Optics Cet. No. 99TH6464, Vol. 3, p. 3 (1999)		
	2	LIM, H. et al., "A novel febrication technique for multiple-wavelength photonic-integrated devices in InGeAs-InGeAs- leser heterostructures", IEEE Photonics Technology Letters, 14:594-6 (May 2002)		
	3	LIU, X. et el., "Control of multiple bendgep shifts in InGaAs-AllinGaAs multiple-quantum-well meteriel using different tribdnesses of PECVD SIOfsub 2/ protection layers", IEEE Photonics Technology Letters 12:1141-2 (2000)		
	4	COI, B., et el., "Selective Quentum-Well intermixing in GaAs-A/GaAs Structures Using Impurity-Free Vecency Diffusion", IEEE J. Q. Elect. 33:1784-1793 (1997)		
	5	AIMEZ, B. et al., "High precision metal masking for multiple wavelength laser clode fabrication using single step ion implentation induced quentum well intermibing," Proc. of the SPIE The International Society for Optical Engineering 4087-907-15 (2000)		
	6	COLDREN, L., "ECE Technical Report 03-02-2002 Reprints of Professor Larry A. Coldren and Colleborators", Dept. of Electrical and Computer Engineering, University of California, Santa Barbara (2002)		
	7	COLDREN, L., "Publication List, Section 18 "Quantum-Weil-Intermixing for Photonic ICs", http://www.aca.ucsb.edu/ Faculty/Coldren/reprints/2002/Reprint/2002/Listo/Pubs.pdf, downloaded 6/9/2006 ad: Dept. of Electrical & Computer Engineering, University of California, Senta Barbara (2003)		
	8	Written Opinion of the ISA/EP in International Application No. PCT/ISB2004/004944, mailed March 11, 2005.		
	9	UNITED KINGDOM PATENT OFFICE, Search Report in UK Patent Application Number G80328808.1, May 25, 2004		
	10	KCCH, T. L. et al., "Tapered Weregulde InGaAsImGaAsP Multiple-Quantum-Well Lasers", IEEE Photonics Technology Letters, 2:88-90 (February 1990)		

#### 

	11	MOERMAN, I. et al., "A Review on Fabrication Technologies for the Monolithic Indegration of Tapers with III-V Semiconductor Devices", IEEE Journal of Selected Topics in Quantum Electronics, 3:1388-1320 (December 1997)	
	12	BROCKAERT, T. et al., "A1As Ekth-Stop Layers for In/GaA1AstInP Heterostructure Devices and Circuits", IEEE Transactions on Electron Devices, Vol 39, No. 3, p. 333-336 (March 1992)	

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Attornou Docket Number		35832 000127		

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That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filling of the information disclosure statement. See 37 CFR 137(eV1).

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- See attached certification statement.
- Fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

Jefferson Perkins

Name/Print

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A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Registration Number

31407

Signature	/Jefferson Perkins/	Date (YYYY-MM-DD)	2006-11-17				

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